

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: )  
)  
Jeng Ping LU et al. ) Group Art Unit: Unknown  
)  
Rule 53(b) Divisional of Prior Application: ) Examiner: Unknown  
Serial No. 09/419,293, filed 10/15/99 )  
)  
Serial No.: Not Yet Assigned )  
)  
For: DUAL DIELECTRIC STRUCTURE )  
FOR SUPPRESSING LATERAL )  
LEAKAGE CURRENT IN HIGH )  
FILL FACTOR ARRAYS )

Commissioner for Patents and Trademarks  
Washington, DC 20231

Sir:

**PRELIMINARY AMENDMENT**

Prior to the examination of the above application, please amend this application  
as follows:

**IN THE CLAIMS:**

Please cancel claims 1-6, without prejudice or disclaimer of the subject matter,  
and add new claims 11-15, as follows:

11. (New) A high fill factor image array formed by:

providing a plurality of source-drain metal contacts;

depositing a first passivation layer;

depositing a second passivation layer over the first passivation layer that

suppresses lateral leakage current;

FINNEGAN  
ENDERSON  
FARABOW  
GARRETT &  
DUNNER LLP

1300 I Street, NW  
Washington, DC 20005  
202.408.4000  
Fax 202.408.4400  
www.finnegan.com

opening a plurality of via holes through the first and second passivation layers;  
depositing a layer of conductive material;  
depositing a first doped a-Si layer;  
patterning to form the collection electrodes;  
depositing a continuous layer of i a-Si;  
depositing a continuous second layer of doped a-Si;  
depositing and patterning an upper conductive layer.

12. (New) The high fill factor image array of claim 11, wherein the first passivation layer comprises at least one of silicon oxynitride, BCB, or a polyamide.

13. (New) The high fill factor image array of claim 11, wherein the second passivation layer is an oxide.

14. (New) The high fill factor image array of claim 11, wherein the second has a thickness of about 1000 Å.

15. (New) The high fill factor image array of claim 11, wherein the wherein the thickness of the second passivation layer is less than the thickness of the first passivation layer.

FINNEGAN  
HENDERSON  
FARABOW  
GARRETT &  
DUNNER LLP

1300 I Street, NW  
Washington, DC 20005  
202.408.4000  
Fax 202.408.4400  
www.finnegan.com

**REMARKS**

In filing the divisional application, Applicants have canceled claims 1-6, without prejudice or disclaimer of the subject matter thereof, and added new claims 11-15.

Claims 7-15 are pending.


Applicants respectfully request early and favorable examination.

If there is any fee due in connection with the filing of this Preliminary Amendment, please charge the fee to our Deposit Account No. 24-0037.

Respectfully submitted,

FINNEGAN, HENDERSON, FARABOW,  
GARRETT & DUNNER, L.L.P.

Dated: February 7, 2002

By:   
Timothy M. Hsieh  
Registration No. 42,672

FINNEGAN  
HENDERSON  
FARABOW  
GARRETT &  
DUNNER LLP

1300 I Street, NW  
Washington, DC 20005  
202.408.4000  
Fax 202.408.4400  
www.finnegan.com